### **MSB1218A-RT1G**

# PNP Silicon General Purpose Amplifier Transistor

This PNP Silicon Epitaxial Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

#### **Features**

- High h<sub>FE</sub>, 210 460
- Low  $V_{CE(sat)}$ , < 0.5 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	45	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	45	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Collector Current - Peak	$I_{C(P)}$	200	mAdc

#### THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P <sub>D</sub>	150	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

#### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage ( $I_C = 2.0 \text{ mAdc}, I_B = 0$ )	V <sub>(BR)CEO</sub>	45	-	Vdc
Collector-Base Breakdown Voltage ( $I_C = 10 \mu Adc, I_E = 0$ )	V <sub>(BR)CBO</sub>	45	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_E = 0$ )	V <sub>(BR)EBO</sub>	7.0	-	Vdc
Collector-Base Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$	I <sub>CBO</sub>	-	0.1	μΑ
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 10 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	100	μΑ
DC Current Gain (Note 2) (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 2.0 mAdc)	h <sub>FE1</sub>	210	340	-
Collector-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>CE(sat)</sub>	-	0.5	Vdc

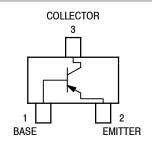
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.
- 2. Pulse Test: Pulse Width ≤ 300 µs, D.C. ≤ 2%.



#### ON Semiconductor®

#### http://onsemi.com





SC-70 (SOT-323) CASE 419 STYLE 4

#### **MARKING DIAGRAM**



BR = Device Code
M = Date Code\*
• Pb-Free Package

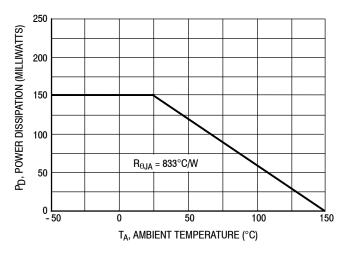
(Note: Microdot may be in either location)
\*Date Code orientation may vary depending
upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MSB1218A-RT1G	SC-70 (Pb-Free)	3000 /Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **MSB1218A-RT1G**



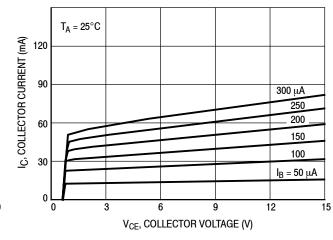
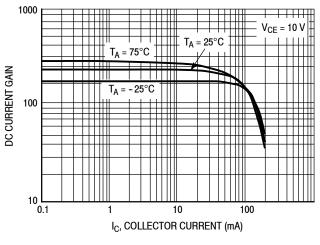


Figure 1. Derating Curve

Figure 2.  $I_C$  -  $V_{CE}$ 



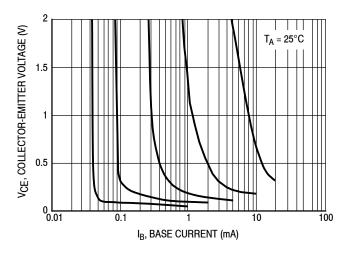
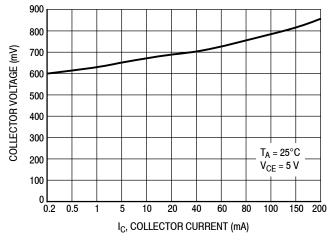


Figure 3. DC Current Gain

Figure 4. Collector Saturation Region



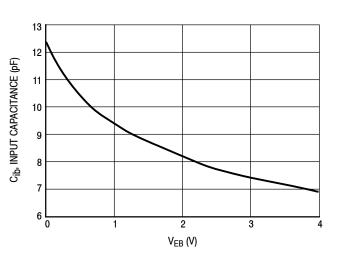


Figure 5. On Voltage

Figure 6. Capacitance

## MSB1218A-RT1G

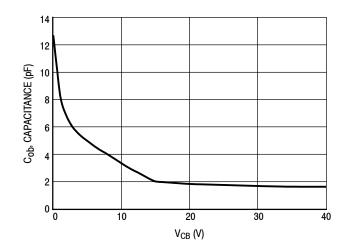


Figure 7. Capacitance







SC-70 (SOT-323) CASE 419 ISSUE R

**DATE 11 OCT 2022** 

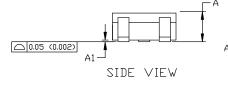
#### NOTES:

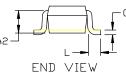
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2	0.70 REF				0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.00	2.20	0.071	0.080	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC				0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	

# SCALE 4:1

TOP VIEW





# GENERIC MARKING DIAGRAM

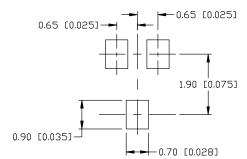


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales